

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 0.625W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: -0.5A$$

Collector-base voltage

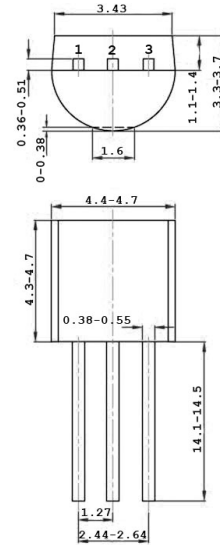
$$V_{(BR)CBO}: -40V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100 \mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-50mA$	64	300	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-500mA$	40		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-500mA, I_B=-50mA$		-0.6	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-500mA, I_B=-50mA$		-1.2	V
Base-emitter voltage	V_{BE}	$I_E=-100mA$		-1.4	V
Transition frequency	f_r	$V_{CE}=-6V, I_C=-20mA$ $f=30MHz$	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F	G	H	I
Range	64-91	78-112	96-135	112-166	144-202	190-300